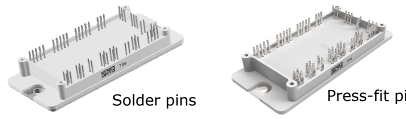
***flow* PIM 2** — **1200 V / 100 A**

Features

- Three-phase rectifier, BRC, Inverter, NTC
- Very Compact housing, easy to route
- IGBT4 / EmCon4 technology for low saturation losses and improved EMC behavior

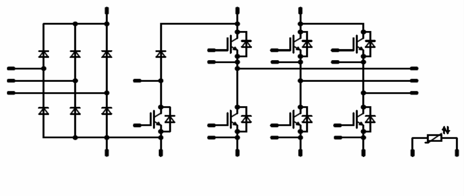
flow 2 17mm housing



Target Applications

- Motor Drives
- Power Generation

Schematic



Types

- V23990-P760-A-PM
- V23990-P760-AY-PM

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Input Rectifier Diode				
Repetitive peak reverse voltage	V_{RRM}		1600	V
Forward current	I_{FAV}		75	A
Surge (non-repetitive) forward current	I_{FSM}	t_p = 10 ms	1000	A
I^2t-value	I^2t		5000	A^2s
Power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	156	W
Maximum Junction Temperature	T_{jmax}		150	°C
Inverter Switch				
Collector-emitter breakdown voltage	V_{CE}		1200	V
DC collector current	I_C		100	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	300	A
Power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	272	W
Gate-emitter peak voltage	V_{GE}		±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j ≤ 150 °C V_{GE} = 15 V	10 800	μs V
Maximum Junction Temperature	T_{jmax}		175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Inverter Diode					
Peak Repetitive Reverse Voltage	V_{RRM}			1200	V
DC forward current	I_F	$T_j = T_{jmax}$	T_s = 80 °C	85	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		200	A
Power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	154	W
Maximum Junction Temperature	T_{jmax}			175	°C
Brake Switch					
Collector-emitter breakdown voltage	V_{CE}			1200	V
DC collector current	I_C			50	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		150	A
Power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	174	W
Gate-emitter peak voltage	V_{GE}			±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j ≤ 150 °C V_{GE} = 15 V		10 800	μs V
Maximum Junction Temperature	T_{jmax}			175	°C
Brake Inverse Diode					
Peak Repetitive Reverse Voltage	V_{RRM}			1200	V
DC forward current	I_F			10	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		20	A
Brake Inverse Diode	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	52	W
Maximum Junction Temperature	T_{jmax}			175	°C
Brake Diode					
Peak Repetitive Reverse Voltage	V_{RRM}			1200	V
DC forward current	I_F			25	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		50	A
Power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	87	W
Maximum Junction Temperature	T_{jmax}			175	°C
Thermal properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{op}			-40…+T_{jmax}-25	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	4000	V
		AC Voltage	t_p = 1 min	2500	V
Creepage distance				min 12,7	mm
Clearance		with Press-fit pins / with Solder pins		11,58 / 11,82	mm
Comparative Tracking Index	CTI			>200	

* 100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_r [V] V_{CE} [V] V_{DS} [V]	I_C [A] I_F [A] I_D [A]	T_j [°C]	Min	Typ	Max	
Input Rectifier Diode										
Forward voltage	V_F				100	25 125		1,18 1,16	1,9	V
Threshold voltage (for power loss calc. only)	V_{to}				100	25 125		0,88 0,75		V
Slope resistance (for power loss calc. only)	r_t				100	25 125		0,003 0,004		Ω
Reverse current	I_r			1500		25 125			0,05 1,1	mA
Thermal resistance junction to heatsink	$R_{th(j\text{-}s)}$	$λ_{paste}$ = 3,4 W/mK (PSX)						0,52		K/W
Inverter Switch										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0034	25	5	5,8	6,5	V
Collector-emitter saturation voltage	V_{CEsat}		15		100	25 150		1,9 2,34	2,5	V
Collector-emitter cut-off current incl. Diode	I_{CES}		0	1200		25			0,03	mA
Gate-emitter leakage current	I_{GES}		20	0		25			700	nA
Integrated Gate resistor	R_{gint}							2		Ω
Turn-on delay time	$t_{d(on)}$	R_{goff} = 4 Ω R_{gon} = 4 Ω	±15	600	100	25 150		126 130		ns
Rise time	t_r					25 150		17 22		ns
Turn-off delay time	$t_{d(off)}$					25 150		242 316		ns
Fall time	t_f					25 150		63 115		ns
Turn-on energy loss	E_{on}					25 150		4,07 6,64		mWs
Turn-off energy loss	E_{off}					25 150		5,22 8,71		mWs
Input capacitance	C_{ies}	f = 1 MHz	0	25		25		5540		pF
Output capacitance	C_{oss}							410		pF
Reverse transfer capacitance	C_{rss}							320		pF
Gate charge	Q_G		±15			25		580		nC
Thermal resistance junction to heatsink	$R_{th(j\text{-}s)}$	$λ_{paste}$ = 3,4 W/mK (PSX)						0,35		K/W
Inverter Diode										
Diode forward voltage	V_F				100	25 150		1,83 1,86	2,4	V
Peak reverse recovery current	I_{RRM}	R_{gon} = 4 Ω	±15	600	100	25 150		167 191		A
Reverse recovery time	t_{rr}					25 150		134 293		ns
Reverse recovered charge	Q_{rr}					25 150		9,39 19,67		μC
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 150		7887 3332		A/μs
Reverse recovered energy	E_{rec}					25 150		3,82 8,55		mWs
Thermal resistance junction to heatsink	$R_{th(j\text{-}s)}$	$λ_{paste}$ = 3,4 W/mK (PSX)						0,62		K/W

Characteristic Values

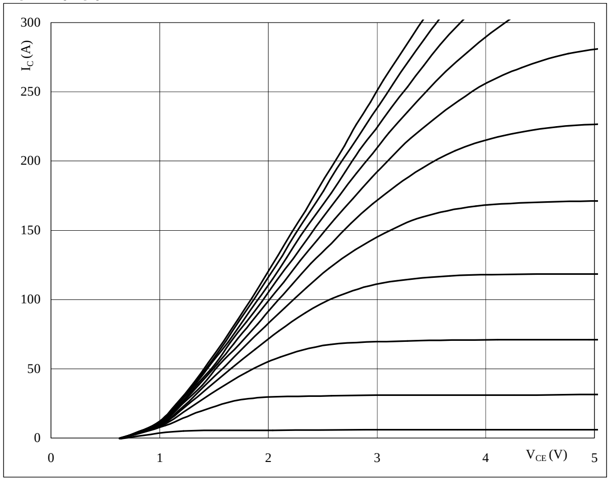
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_r [V] V_{CE} [V] V_{DS} [V]	I_C [A] I_F [A] I_D [A]	T_j [°C]	Min	Typ	Max	
Brake Switch										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0017	25	5	5,8	6,5	V
Collector-emitter saturation voltage	V_{CEsat}		15		50	25 150		1,84 2,27	2,3	V
Collector-emitter cut-off incl diode	I_{CES}		0	1200		25			0,25	mA
Gate-emitter leakage current	I_{GES}		20	0		25			700	nA
Integrated Gate resistor	R_{gint}							4		Ω
Turn-on delay time	$t_{d(on)}$					25 150		117 121		
Rise time	t_r					25 150		18 24		ns
Turn-off delay time	$t_{d(off)}$	R_{goff} = 8 Ω R_{gon} = 8 Ω	±15	600	50	25 150		249 316		
Fall time	t_f					25 150		88 125		
Turn-on energy loss	E_{on}					25 150		2,39 3,43		mWs
Turn-off energy loss	E_{off}					25 150		2,96 4,8		
Input capacitance	C_{ies}							2770		
Output capacitance	C_{oss}	f = 1 MHz	0	25		25		205		pF
Reverse transfer capacitance	C_{rss}							160		
Gate charge	Q_G		±15	960		25		290		nC
Thermal resistance junction to heatsink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,55		K/W
Brake Inverse Diode										
Diode forward voltage	V_F				10	25 150	1,1	1,84 1,8	2,1	V
Thermal resistance junction to heatsink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,68		K/W
Brake Diode										
Diode forward voltage	V_F				25	25 150		1,87 1,83	2,2	V
Reverse leakage current	I_r			600		25			10	µA
Peak reverse recovery current	I_{RRM}					25 150		54,29 78,18		A
Reverse recovery time	t_{rr}					25 150		158,7 295,4		ns
Reverse recovered charge	Q_{rr}	R_{gon} = 8 Ω	±15	600	50	25 150		3,21 6,6		µC
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 150		4114 3412		A/µs
Reverse recovery energy	E_{rec}					25 150		3,21 6,6		mWs
Thermal resistance junction to heatsink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,09		K/W
Thermistor										
Rated resistance	R_{25}					25	20,9	22	23,1	kΩ
Deviation of R_{100}	$D_{R/R}$	R_{100}=1486 Ω				100		2,9		%
Power dissipation	P					25		210		mW
Power dissipation constant	$B_{(25/100)}$	Tol. ±3%				25		2		K

Output Inverter

figure 1. IGBT

Typical output characteristics

$I_C = f(V_{CE})$



At

t_p = 250 µs

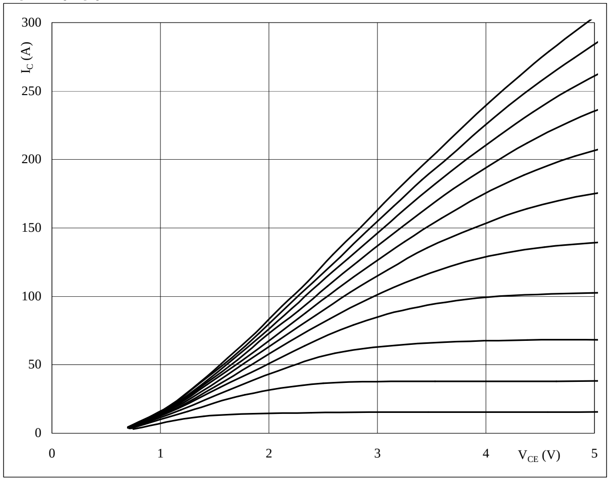
T_j = 25 °C

VGE from 7 V to 17 V in steps of 1 V

figure 2. IGBT

Typical output characteristics

$I_C = f(V_{CE})$



At

t_p = 250 µs

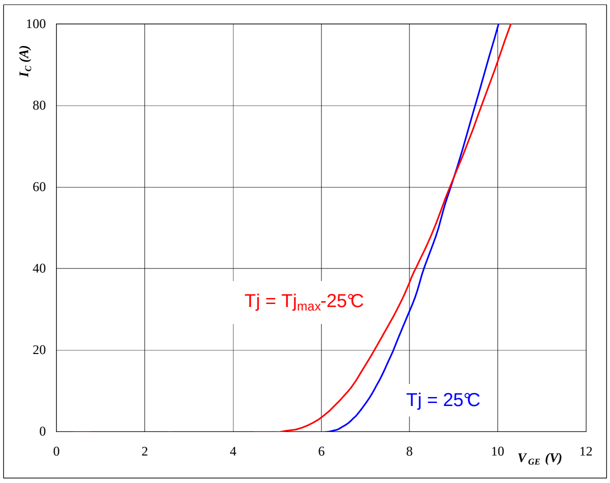
T_j = 150 °C

VGE from 7 V to 17 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

$I_c = f(V_{GE})$



At

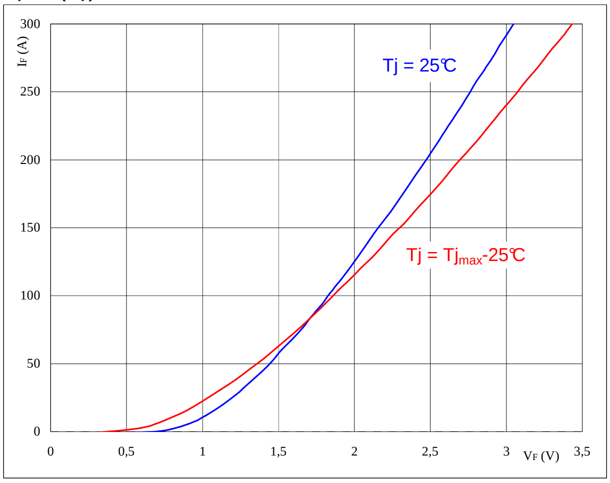
t_p = 250 µs

V_{CE} = 10 V

figure 4. FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

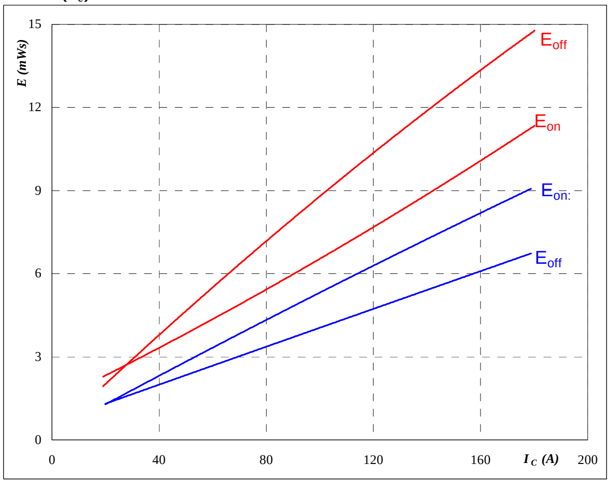
t_p = 250 µs

Output Inverter

figure 5.	**IGBT**

Typical switching energy losses
as a function of collector current

$E = f(I_c)$



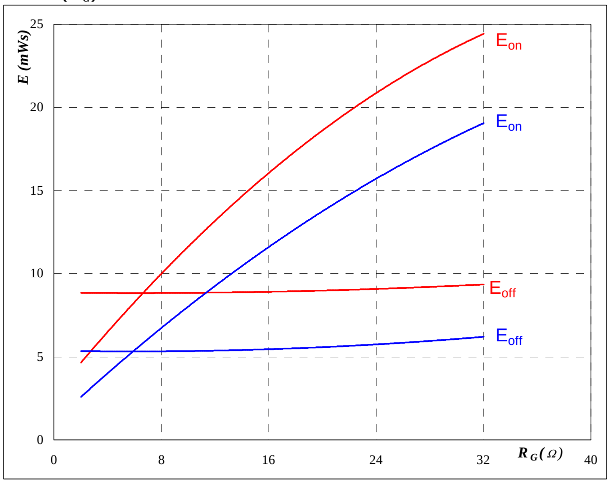
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

figure 6.	**IGBT**

Typical switching energy losses
as a function of gate resistor

$E = f(R_G)$



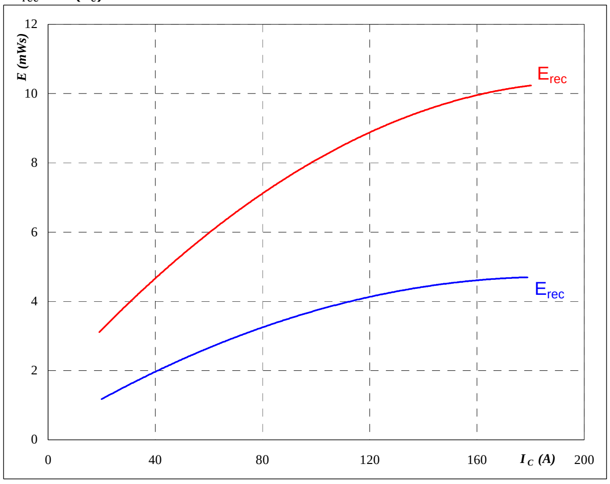
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	100	A

figure 7.	**IGBT**

Typical reverse recovery energy loss
as a function of collector current

$E_{rec} = f(I_c)$



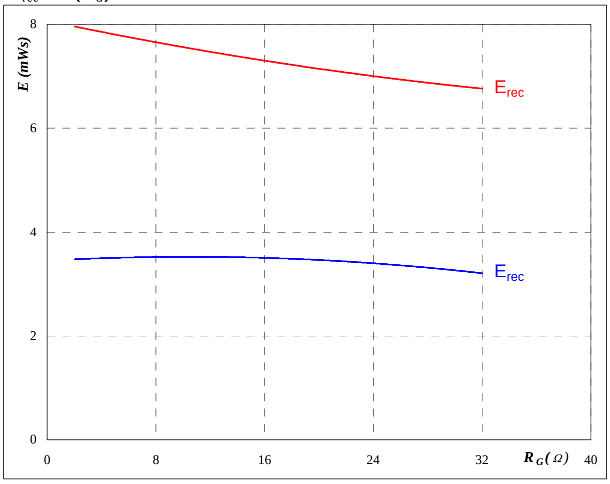
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

figure 8.	**IGBT**

Typical reverse recovery energy loss
as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

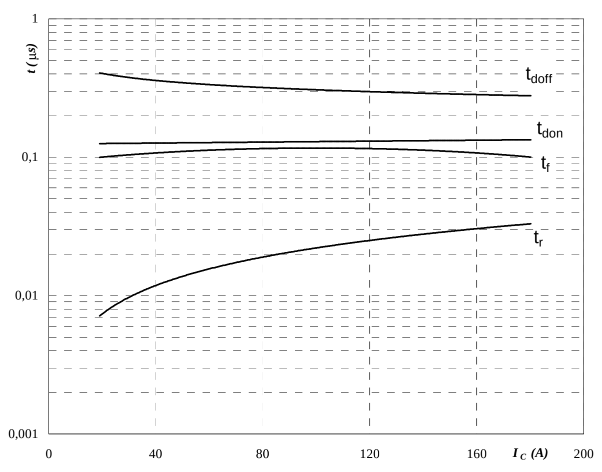
T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	100	A

Output Inverter

figure 9. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



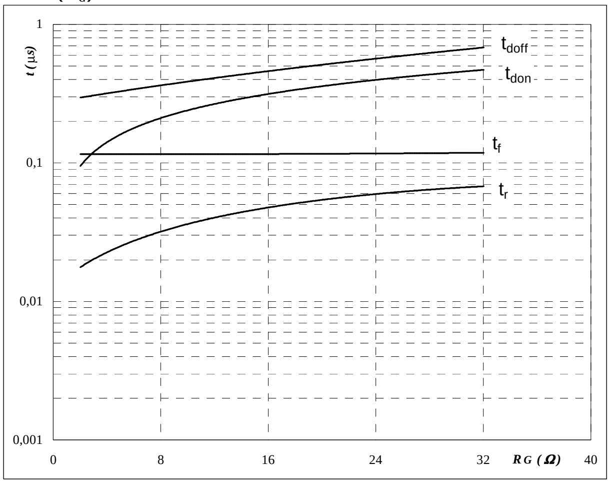
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

figure 10. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_G)$



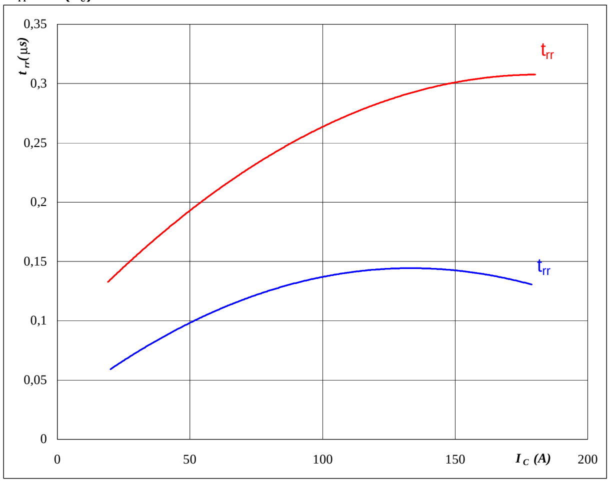
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	100	A

figure 11. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_c)$



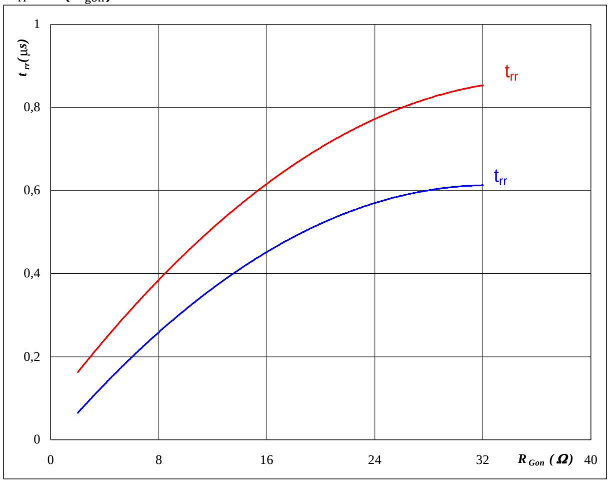
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

figure 12. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



At

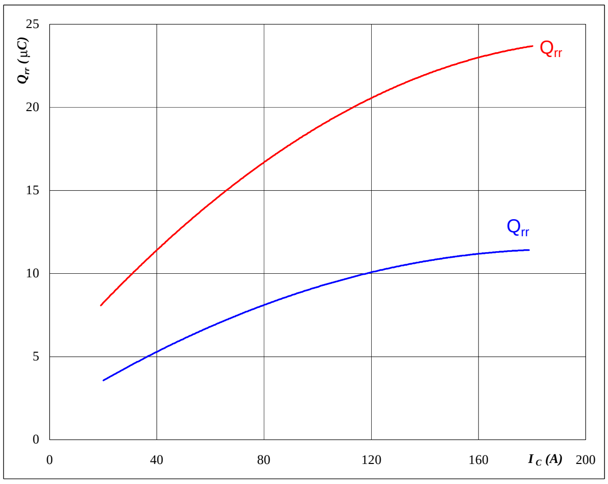
T_j =	25/150	°C
V_R =	600	V
I_F =	100	A
V_{GE} =	±15	V

Output Inverter

figure 13. **FWD**

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_c)$



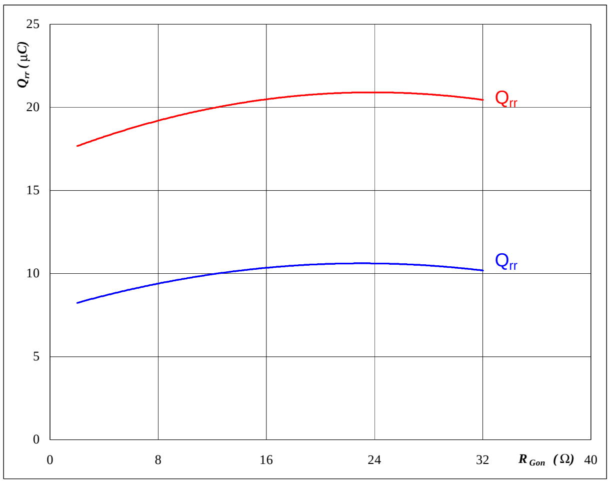
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

figure 14. **FWD**

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



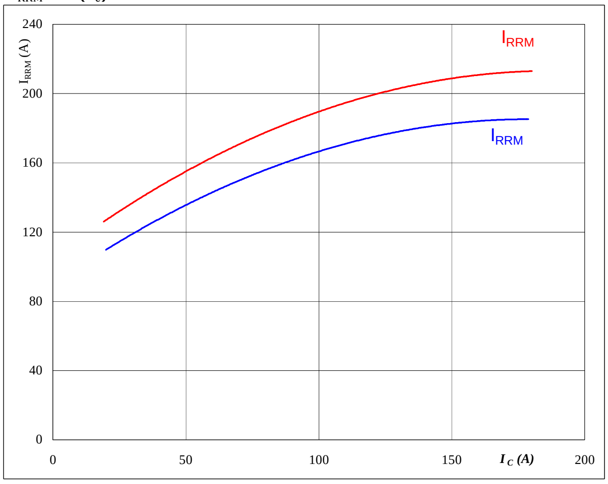
At

T_j =	25/150	°C
V_R =	600	V
I_F =	100	A
V_{GE} =	±15	V

figure 15. **FWD**

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_c)$



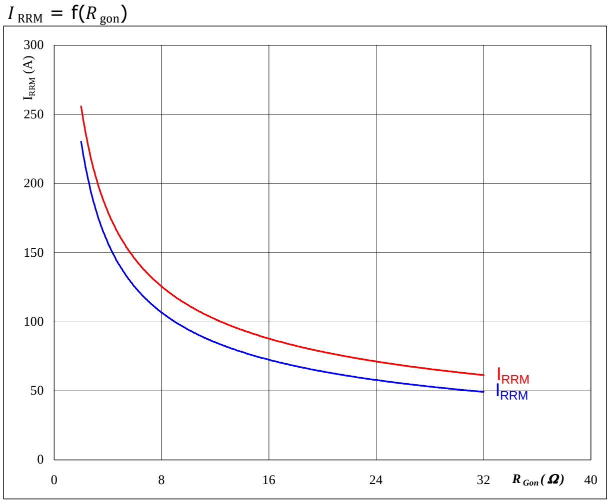
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

figure 16. **FWD**

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

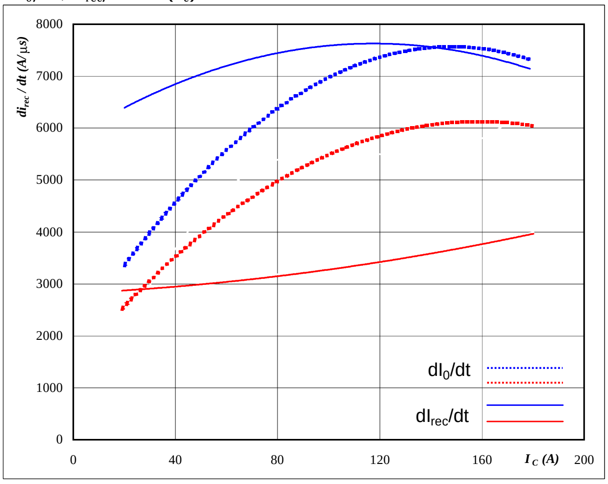
T_j =	25/150	°C
V_R =	600	V
I_F =	100	A
V_{GE} =	±15	V

Output Inverter

figure 17. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(I_c)$



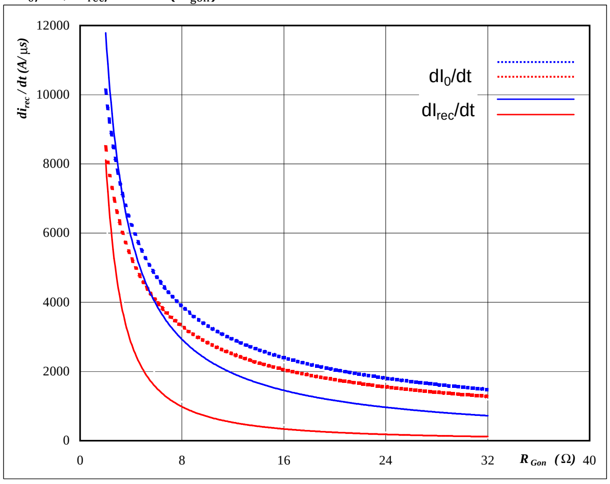
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

figure 18. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



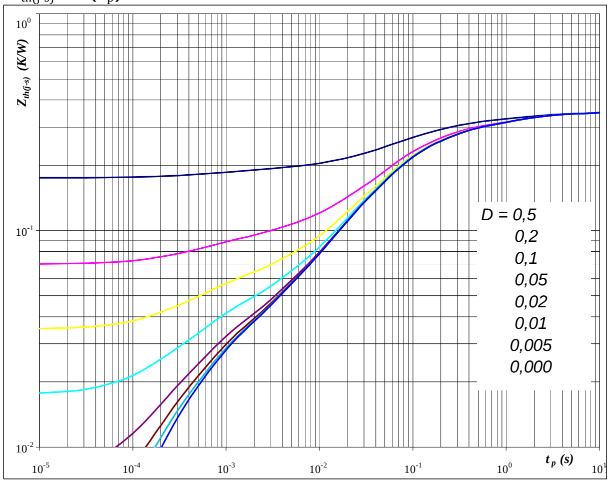
At

T_j =	25/150	°C
V_R =	600	V
I_F =	100	A
V_{GE} =	±15	V

figure 19.

IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



At

$D = t_p / T$

$R_{th(j-s)}$ = 0,35 K/W

Single device heated

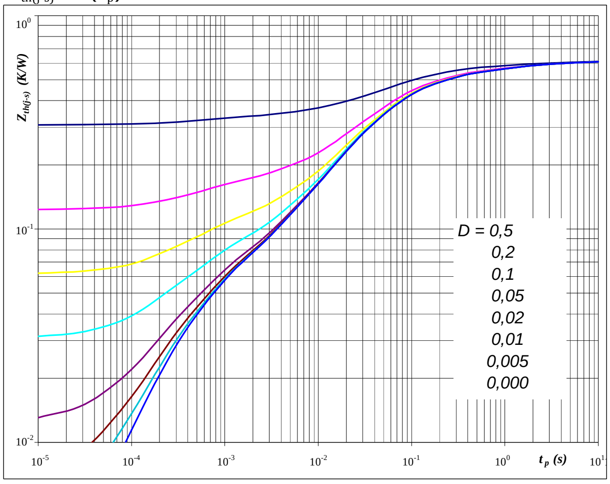
IGBT thermal model values

R (K/W)	Tau (s)
6,03E-02	1,65E+00
7,55E-02	2,28E-01
1,42E-01	5,83E-02
4,00E-02	1,39E-02
1,37E-02	1,77E-03
1,79E-02	3,82E-04

figure 20.

FWD transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



At

$D = t_p / T$

$R_{th(j-s)}$ = 0,62 K/W

Single device heated

FWD thermal model values

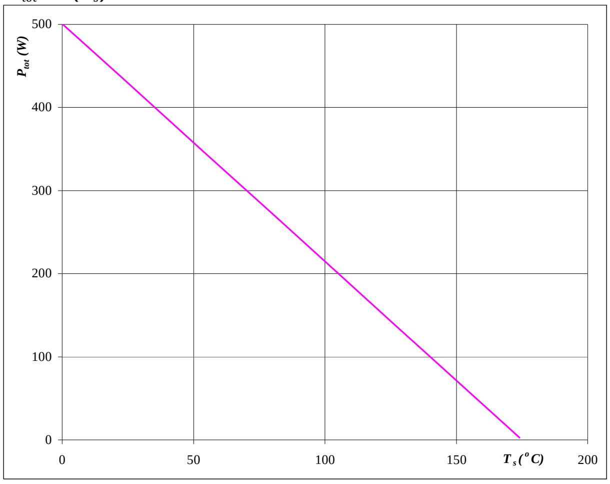
R (K/W)	Tau (s)
2,75E-02	6,85E+00
5,51E-02	1,37E+00
8,48E-02	2,76E-01
2,34E-01	6,50E-02
1,48E-01	1,93E-02
2,67E-02	2,38E-03
3,98E-02	3,81E-04

Output Inverter

figure 21. **IGBT**

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_s)$



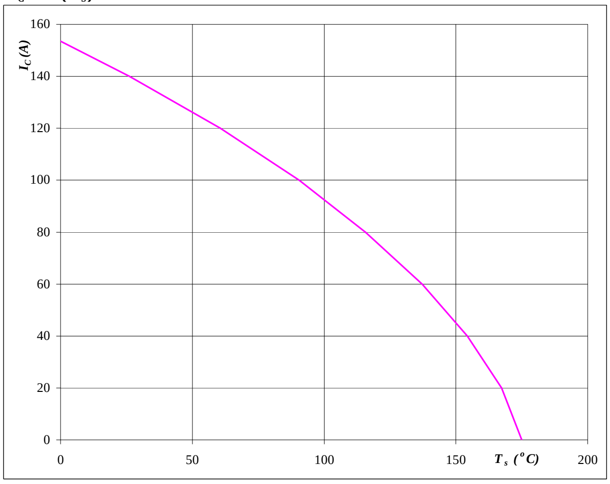
At

T_j = 175 °C

figure 22. **IGBT**

Collector current as a function of heatsink temperature

$I_C = f(T_s)$



At

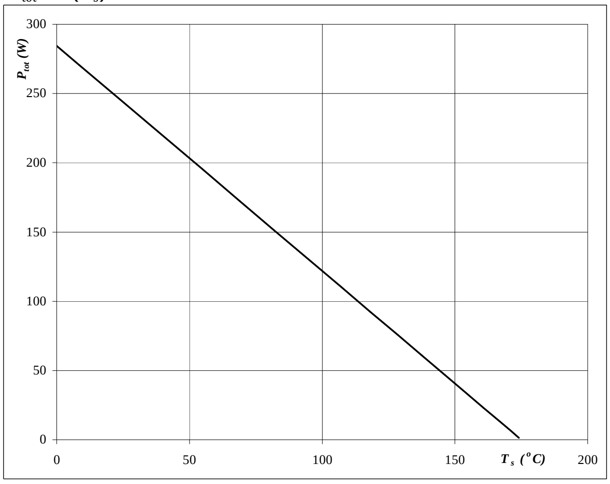
T_j = 175 °C

V_{GE} = 15 V

figure 23. **FWD**

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_s)$



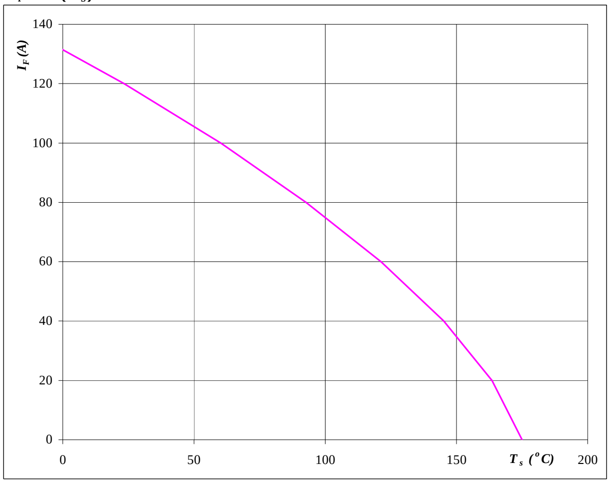
At

T_j = 175 °C

figure 24. **FWD**

Forward current as a function of heatsink temperature

$I_F = f(T_s)$



At

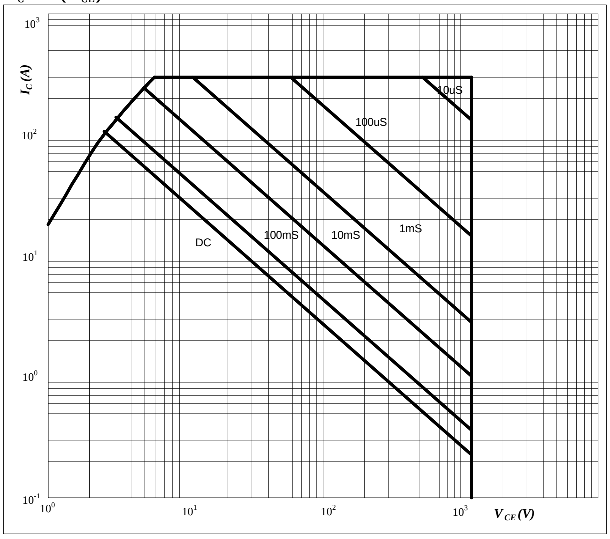
T_j = 175 °C

Output Inverter

figure 25. **IGBT**

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$



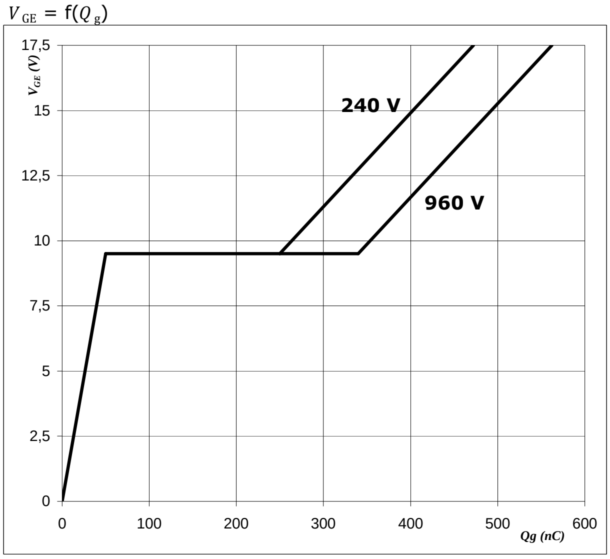
At

D =	single pulse	
T_s =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	

figure 26. **IGBT**

Gate voltage vs Gate charge

$V_{GE} = f(Q_g)$



At

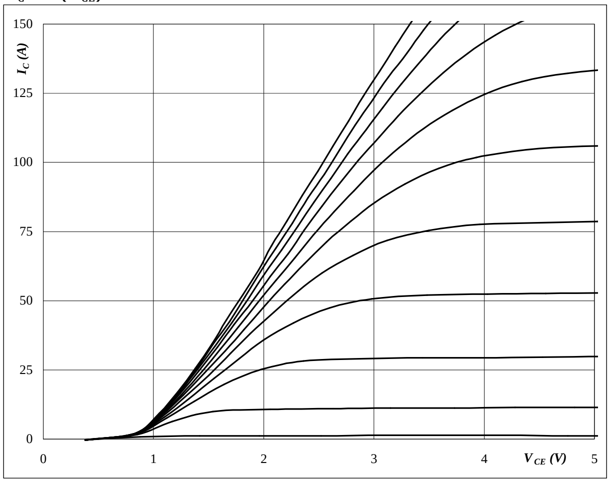
I_C =	100	A

Brake

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$



At

t_p = 250 µs

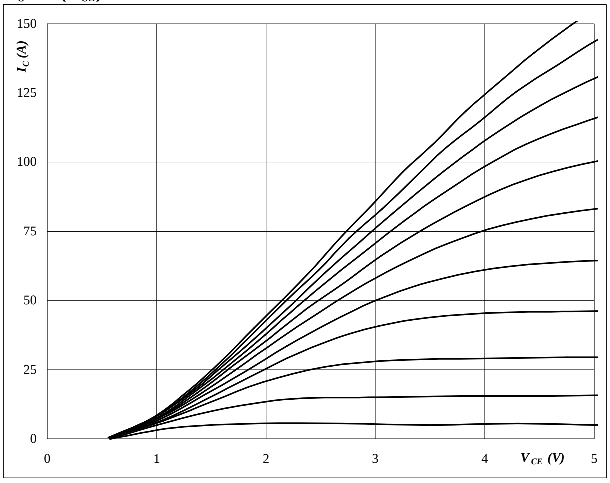
T_j = 25 °C

VGE from 7 V to 17 V in steps of 1 V

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$



At

t_p = 250 µs

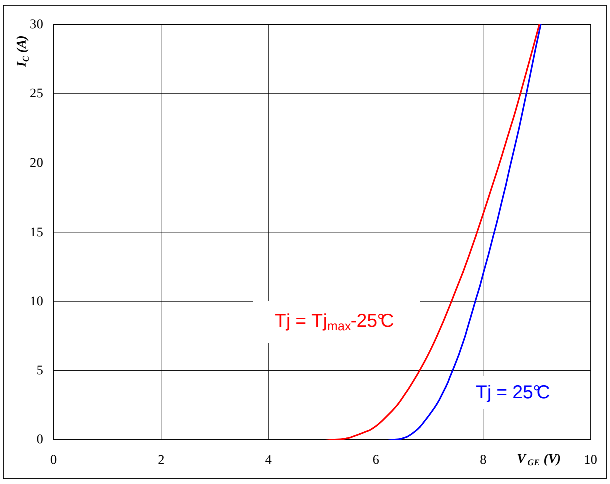
T_j = 150 °C

VGE from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$



At

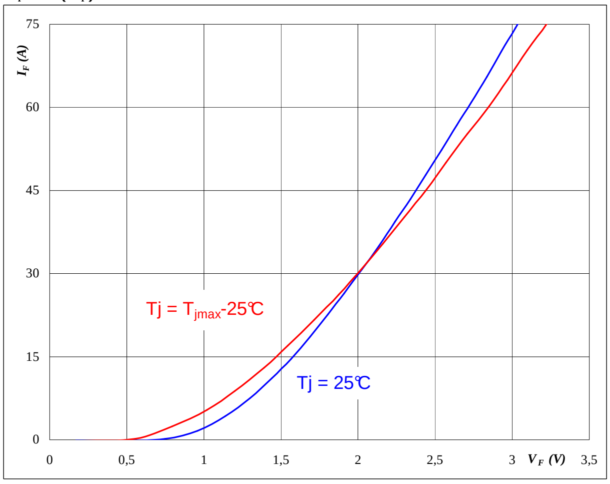
t_p = 250 µs

V_{CE} = 10 V

figure 4. **FWD**

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

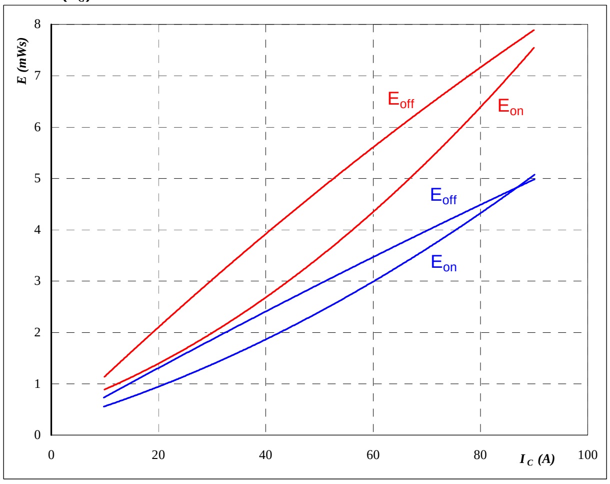
t_p = 250 µs

Brake

figure 5.	IGBT

Typical switching energy losses
as a function of collector current

$E = f(I_C)$



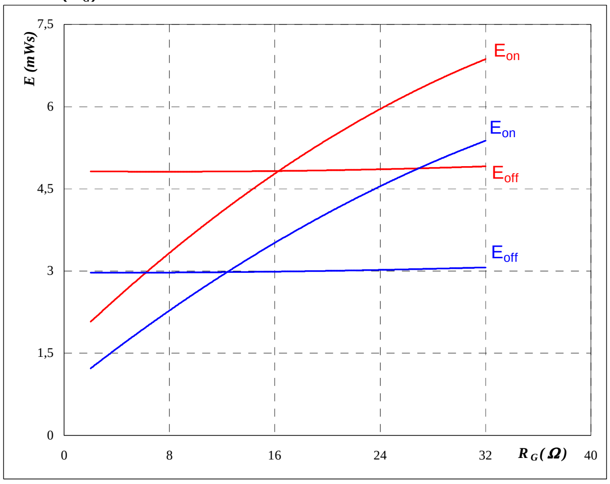
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

figure 6.	IGBT

Typical switching energy losses
as a function of gate resistor

$E = f(R_G)$



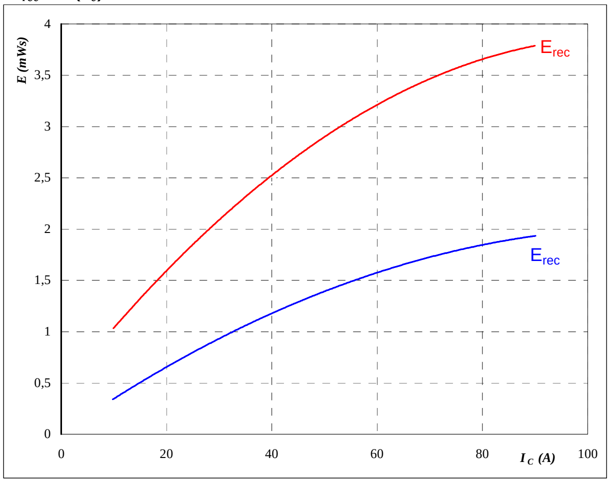
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	50	A

figure 7.	IGBT

Typical reverse recovery energy loss
as a function of collector current

$E_{rec} = f(I_c)$



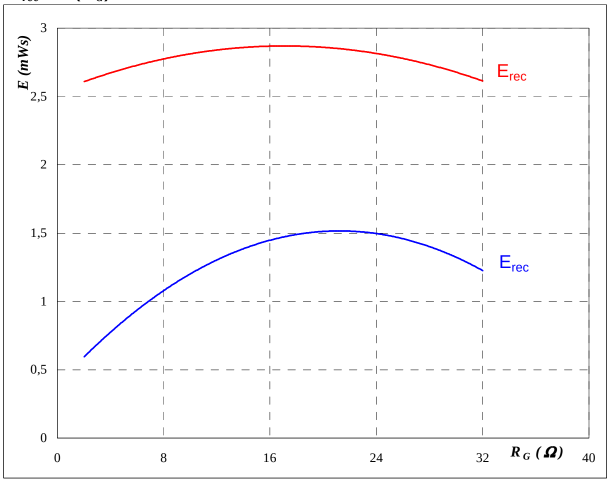
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	8	Ω

figure 8.	IGBT

Typical reverse recovery energy loss
as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

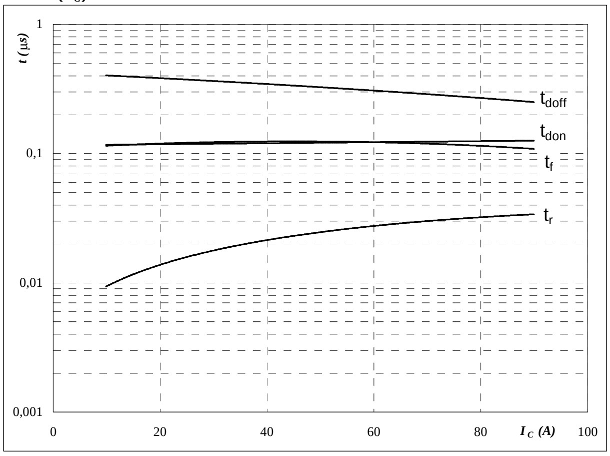
T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	50	A

Brake

figure 9. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



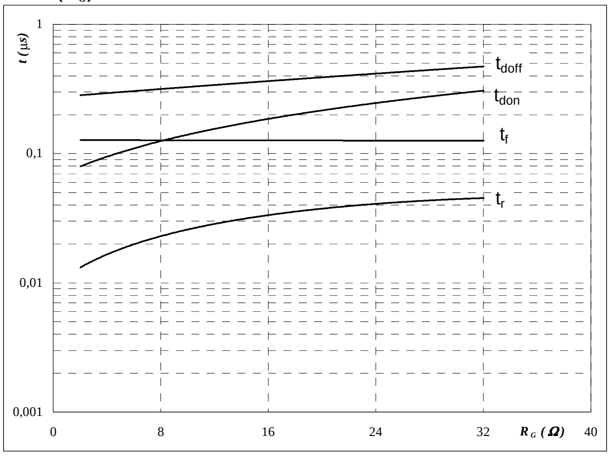
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

figure 10. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_G)$



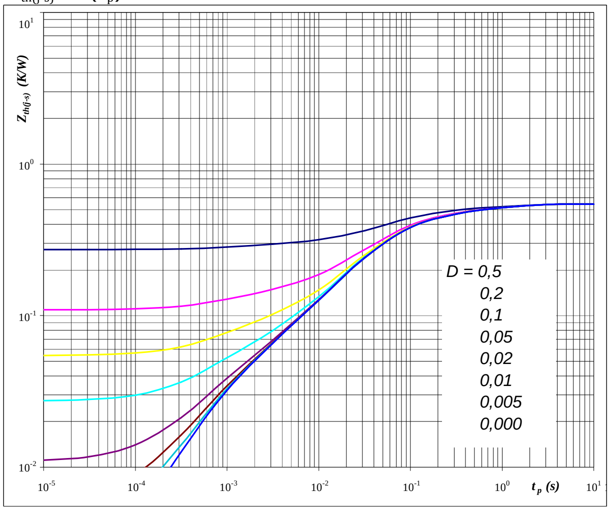
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	50	A

figure 11. **IGBT**

IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



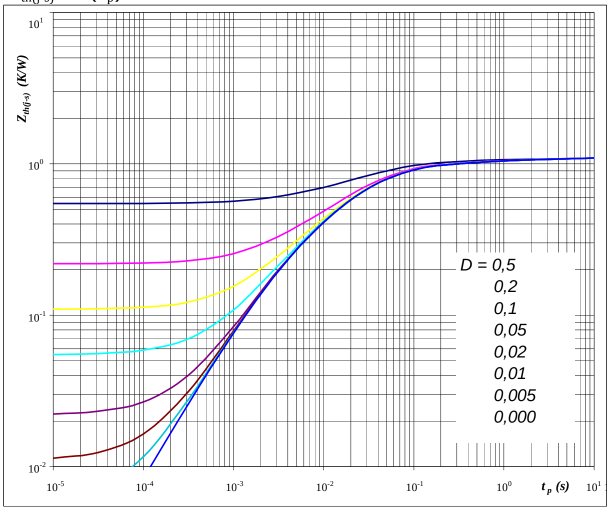
At

D =	t_p / T	
$R_{th(j-s)}$ =	0,54	K/W

figure 12. **FWD**

FWD transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



At

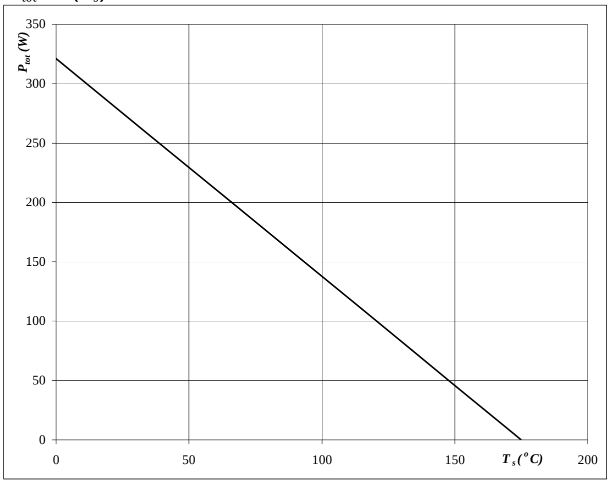
D =	t_p / T	
$R_{th(j-s)}$ =	1,09	K/W

Brake

figure 13. **IGBT**

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_s)$



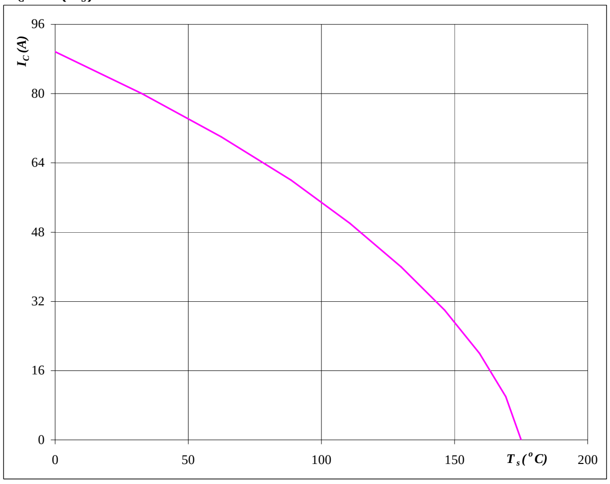
At

T_j = 175 ºC

figure 14. **IGBT**

Collector current as a function of heatsink temperature

$I_C = f(T_s)$



At

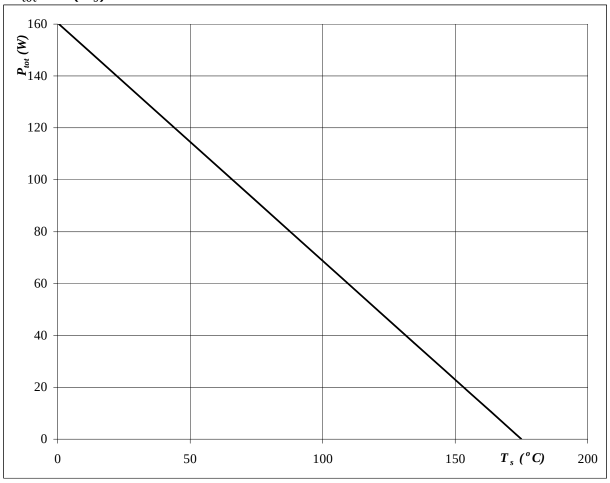
T_j = 175 ºC

V_{GE} = 15 V

figure 15. **FWD**

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_s)$



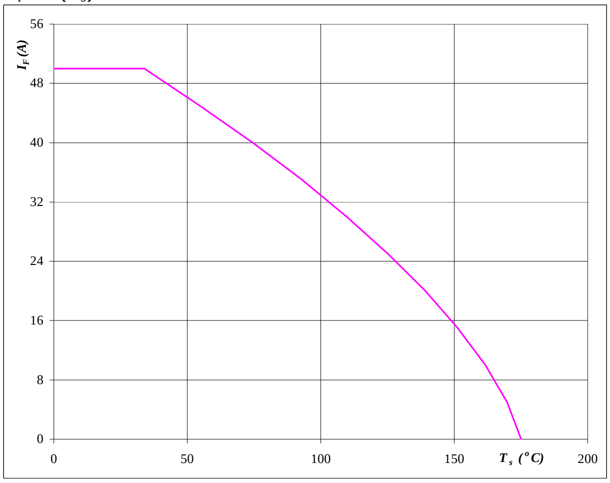
At

T_j = 175 ºC

figure 16. **FWD**

Forward current as a function of heatsink temperature

$I_F = f(T_s)$



At

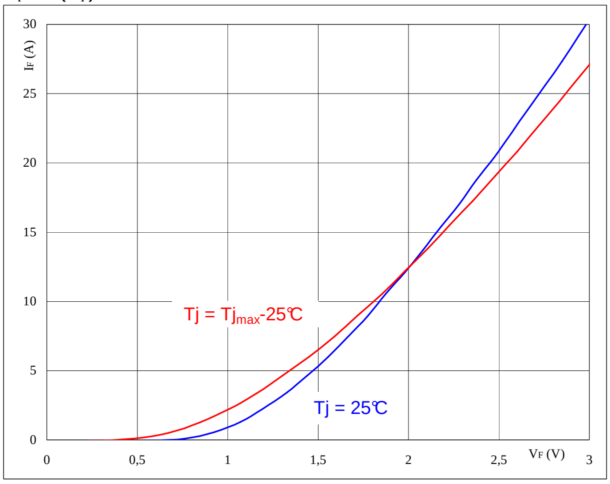
T_j = 175 ºC

Brake Inverse Diode

figure 1. **Brake Inverse Diode**

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



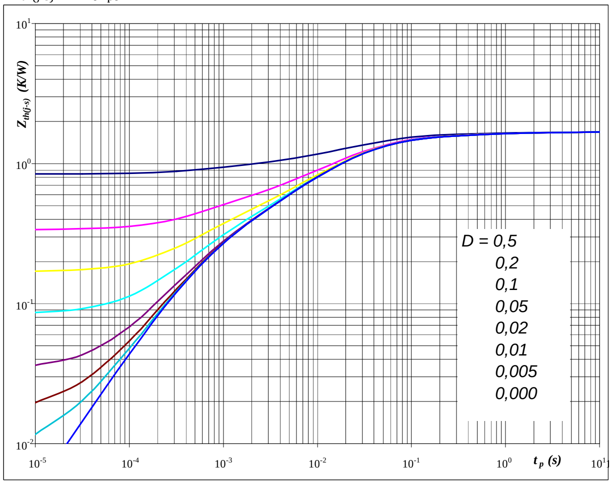
At

t_p = 250 µs

figure 2. **Brake Inverse Diode**

Diode transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



At

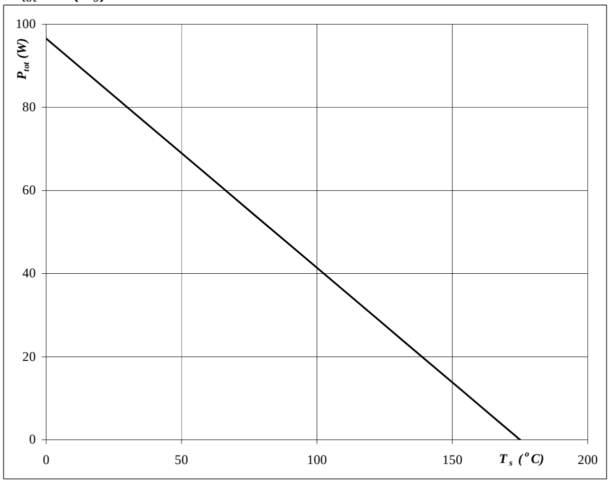
$D = t_p / T$

$R_{th(j-s)}$ = 1,68 K/W

figure 3. **Brake Inverse Diode**

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_s)$



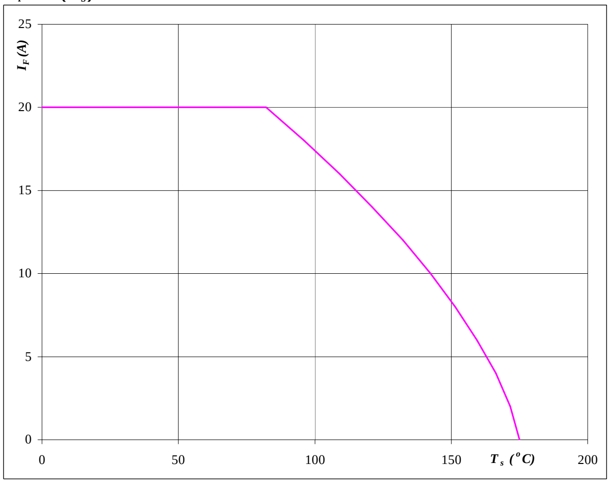
At

T_j = 175 ºC

figure 4. **Brake Inverse Diode**

Forward current as a function of heatsink temperature

$I_F = f(T_s)$



At

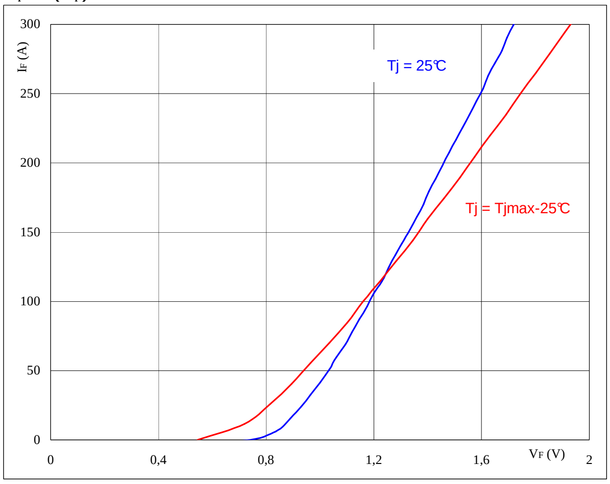
T_j = 175 ºC

Input Rectifier Diode

figure 1. **Rectifier Diode**

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



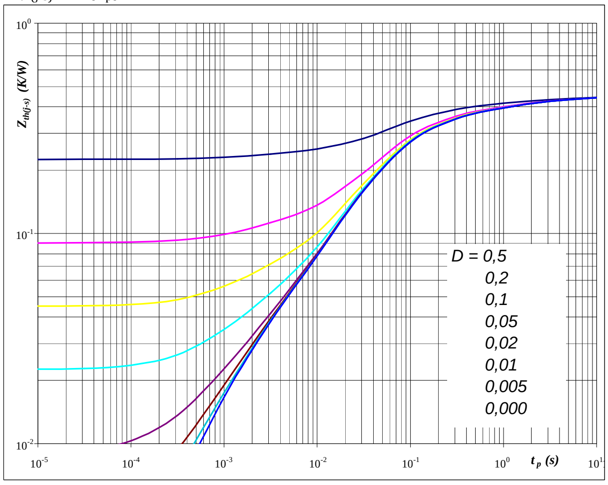
At

t_p = 250 μs

figure 2. **Rectifier Diode**

Diode transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



At

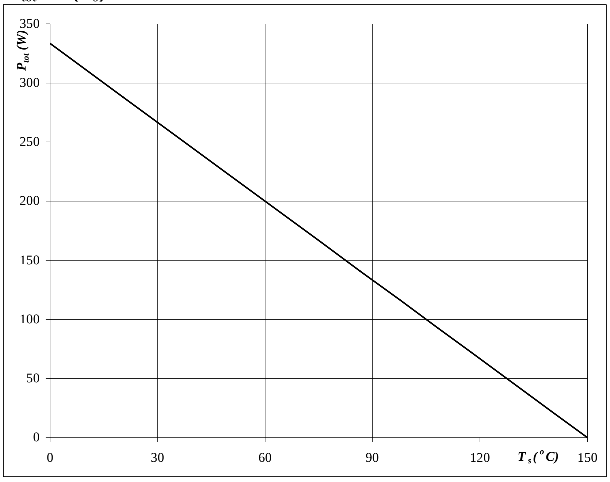
D = t_p / T

$R_{th(j-s)}$ = 0,45 K/W

figure 3. **Rectifier Diode**

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_s)$



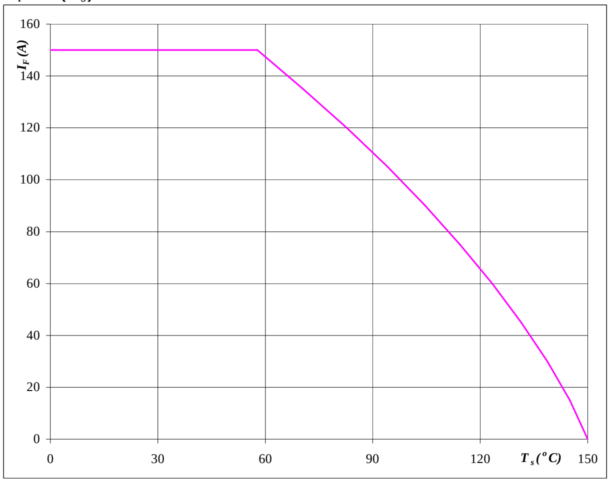
At

T_j = 150 ºC

figure 4. **Rectifier Diode**

Forward current as a function of heatsink temperature

$I_F = f(T_s)$



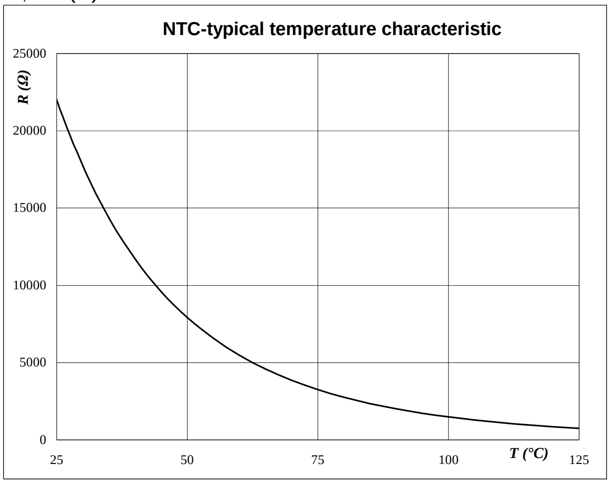
At

T_j = 150 ºC

Thermistor

figure 1.	Thermistor

Typical NTC characteristic
as a function of temperature
$R_T = f(T)$



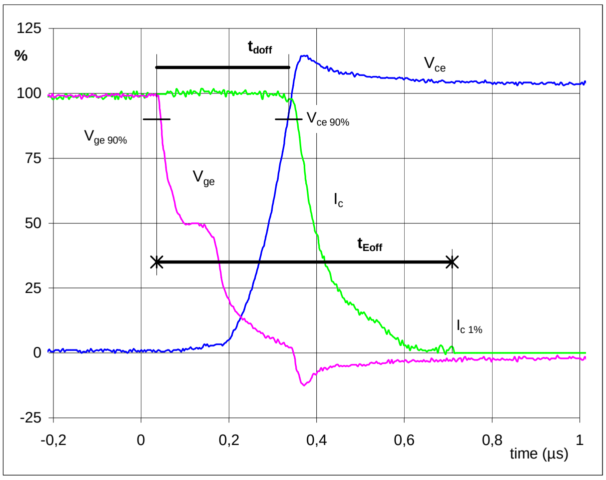
Switching Definitions Output Inverter

General conditions

T_j	=	125 °C
R_{gon}	=	4 Ω
R_{goff}	=	4 Ω

figure 1. **IGBT**

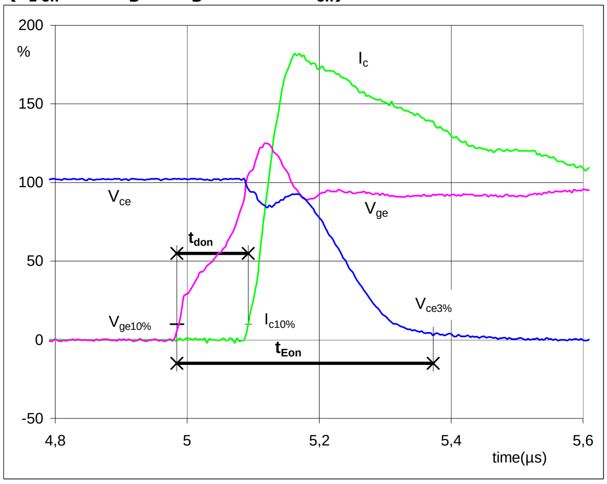
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff}
($t_{E\,off}$ = integrating time for E_{off})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	100	A
t_{doff} =	0,29	µs
$t_{E\,off}$ =	0,67	µs

figure 2. **IGBT**

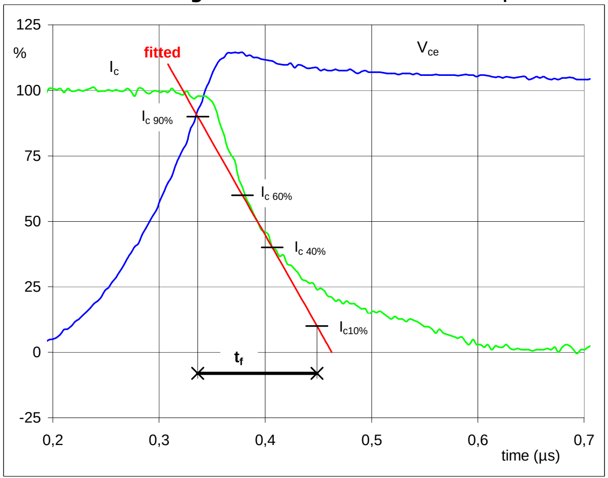
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon}
($t_{E\,on}$ = integrating time for E_{on})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	100	A
t_{don} =	0,11	µs
$t_{E\,on}$ =	0,39	µs

figure 3. **IGBT**

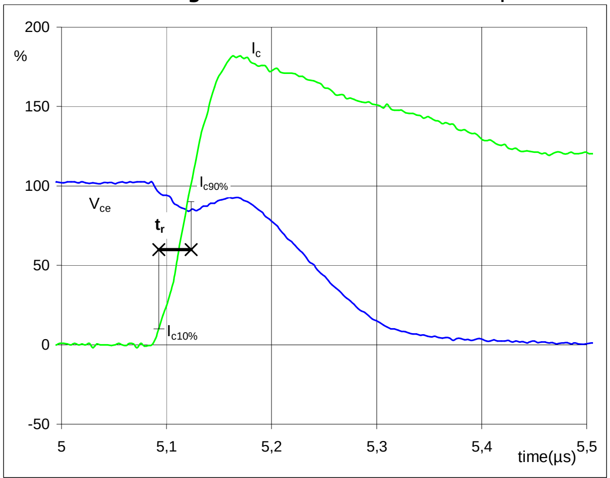
Turn-off Switching Waveforms & definition of t_f



V_C (100%) =	600	V
I_C (100%) =	100	A
t_f =	0,11	µs

figure 4. **IGBT**

Turn-on Switching Waveforms & definition of t_r

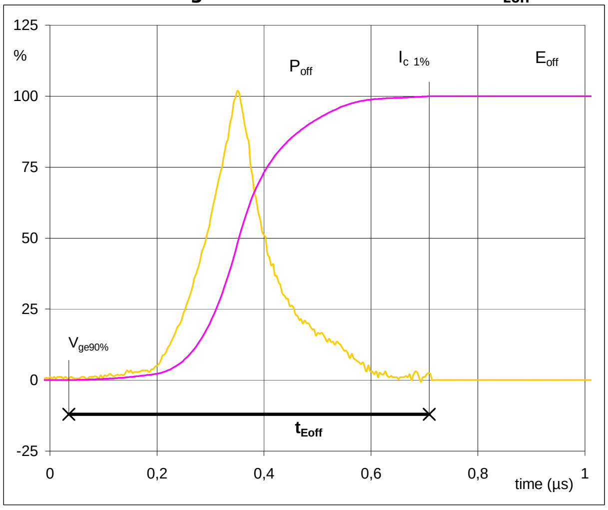


V_C (100%) =	600	V
I_C (100%) =	100	A
t_r =	0,03	µs

Switching Definitions Output Inverter

figure 5. **IGBT**

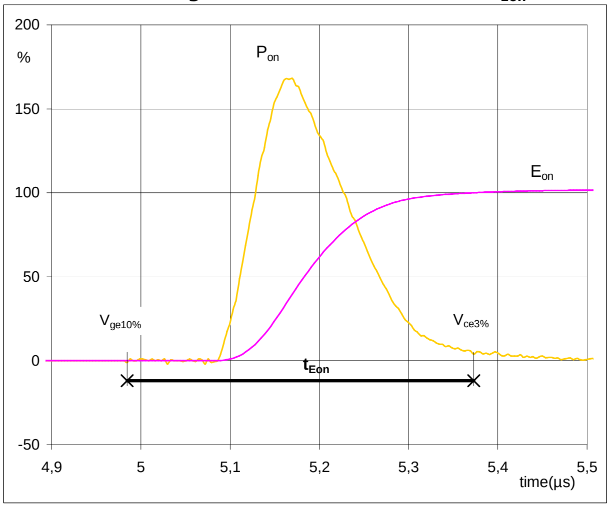
Turn-off Switching Waveforms & definition of t_{Eoff}



P_{off} (100%) =	59,91	kW
E_{off} (100%) =	8,87	mJ
$t_{E\,off}$ =	0,67	µs

figure 6. **IGBT**

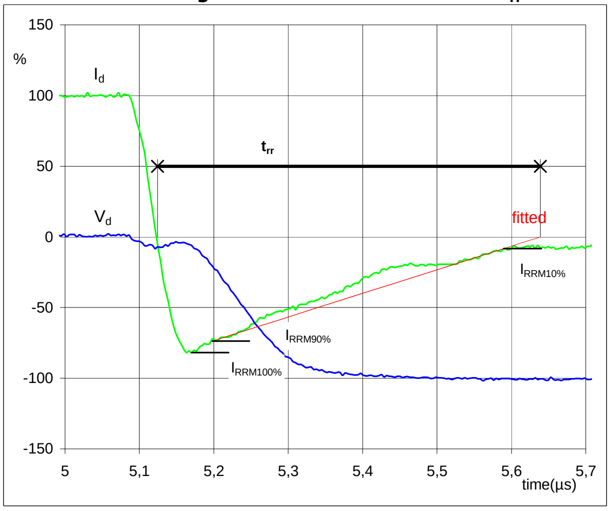
Turn-on Switching Waveforms & definition of t_{Eon}



P_{on} (100%) =	59,91	kW
E_{on} (100%) =	12,48	mJ
$t_{E\,on}$ =	0,39	µs

figure 7. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

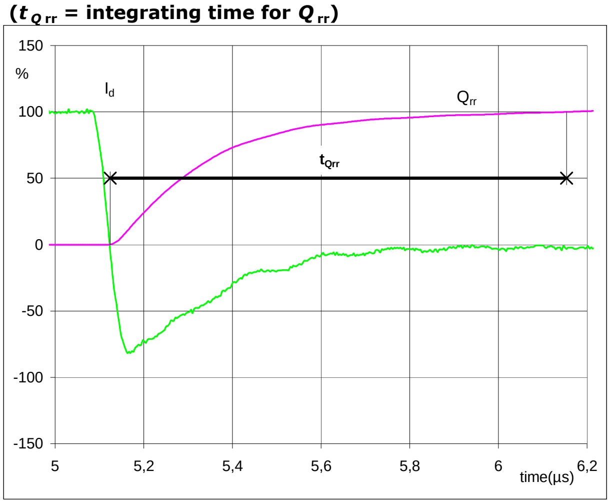


V_d (100%) =	600	V
I_d (100%) =	100	A
I_{RRM} (100%) =	-83	A
t_{rr} =	0,51	µs

Switching Definitions Output Inverter

figure 8. **FWD**

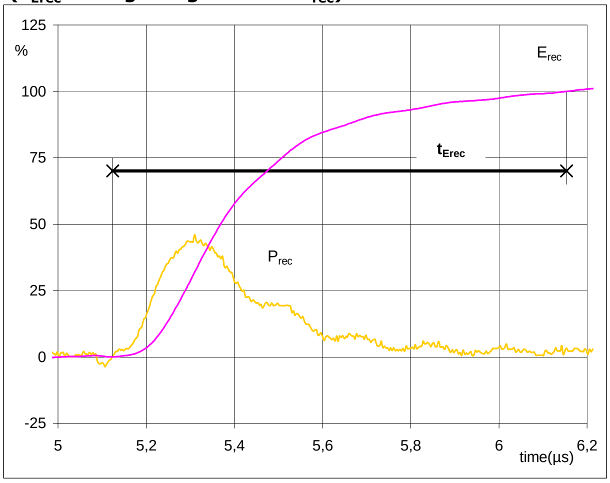
Turn-on Switching Waveforms & definition of t_{Qrr}
($t_{Q\,rr}$ = integrating time for Q_{rr})



I_d (100%) =	100	A
Q_{rr} (100%) =	20,73	µC
t_{Qint} =	1,03	µs

figure 9. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec}
(t_{Erec}= integrating time for E_{rec})



P_{rec} (100%) =	59,91	kW
E_{rec} (100%) =	7,85	mJ
$t_{E\,rec}$ =	1,03	µs

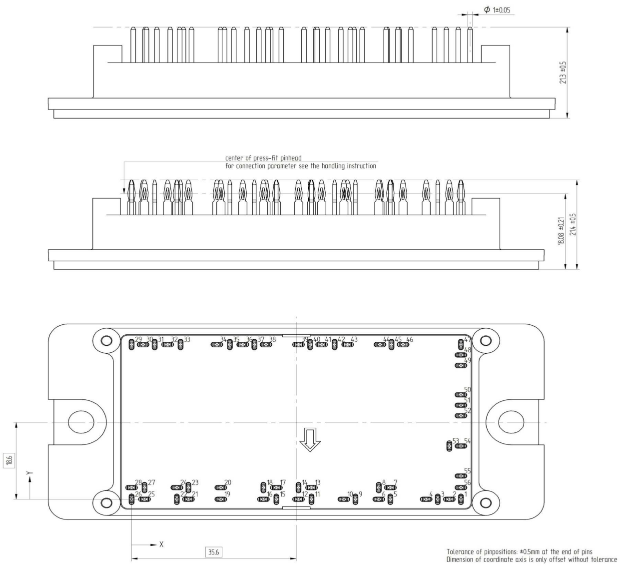
Ordering Code & Marking

Version	Ordering Code
without thermal paste with solder pins	V23990-P760-A-PM
without thermal paste with Press-fit pins	V23990-P760-AY-PM
with thermal paste with solder pins	V23990-P760-A-/3/-PM
with thermal paste with Press-fit pins	V23990-P760-AY-/3/-PM

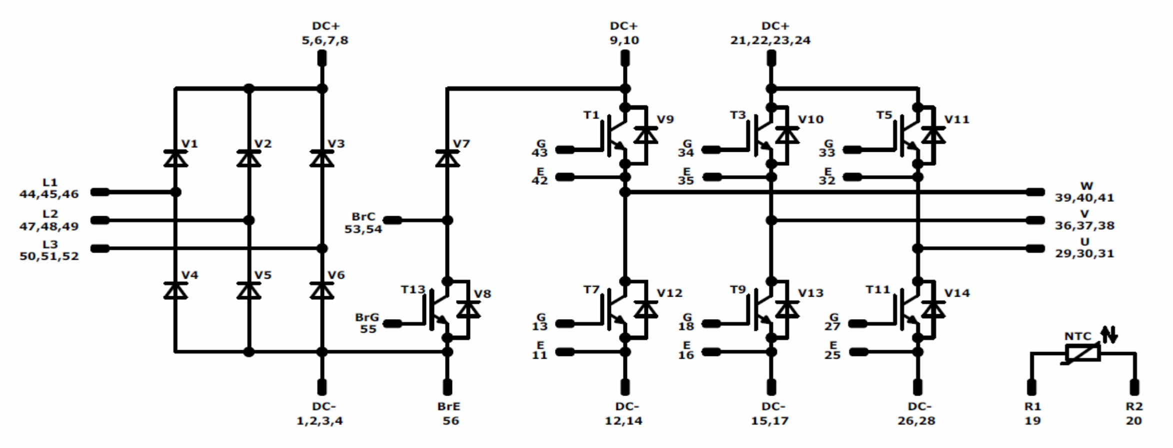
Text	**VIN**	**Date code**	**Name&Ver**	**UL**	**Lot**	**Serial**
	VIN	WWYY	NNNNNNVV	UL	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

Pin table [mm]				Pin table [mm]			
Pin	Func	X	Y	Pin	Func	X	Y
1	DC-	71,2	0	29	U	0	37,2
2	DC-	68,7	0	30	U	2,5	37,2
3	DC-	66,2	0	31	U	5	37,2
4	DC-	63,7	0	32	E	7,8	37,2
5	DC+	55,95	0	33	G	10,6	37,2
6	DC+	53,45	0	34	G	18,45	37,2
7	DC+	55,95	2,8	35	E	21,25	37,2
8	DC+	53,45	2,8	36	V	24,05	37,2
9	DC+	48,4	0	37	V	26,55	37,2
10	DC+	45,9	0	38	V	29,05	37,2
11	E	38,9	0	39	W	36,1	37,2
12	DC-	36,1	0	40	W	38,6	37,2
13	G	38,9	2,8	41	W	41,1	37,2
14	DC-	36,1	2,8	42	E	43,9	37,2
15	DC-	31,3	0	43	G	46,7	37,2
16	E	28,5	0	44	L1	53,7	37,2
17	DC-	31,3	2,8	45	L1	56,2	37,2
18	G	28,5	2,8	46	L1	58,7	37,2
19	R2	19,3	0	47	L2	71,2	37,2
20	R1	19,3	2,8	48	L2	71,2	34,7
21	DC+	12,3	0	49	L2	71,2	32,2
22	DC+	9,8	0	50	L3	71,2	25,2
23	DC+	12,3	2,8	51	L3	71,2	22,7
24	DC+	9,8	2,8	52	L3	71,2	20,2
25	E	2,8	0	53	BrC	71,2	12,8
26	DC-	0	0	54	BrC	68,7	12,8
27	G	2,8	2,8	55	BrG	71,2	5,6
28	DC-	0	2,8	56	BrE	71,2	2,8



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T1,T3,T5,T7,T9,T11	IGBT	1200 V	100 A	Inverter Switch	
V9-V14	FWD	1200 V	100 A	Inverter Diode	
V1-V6	Rectifier	1600 V	75 A	Input Rectifier Diode	
T13	IGBT	1200 V	50 A	Brake Switch	
V7	FWD	1200 V	25 A	Brake Diode	
V8	FWD	1200 V	10 A	Brake Inverse Diode	
NTC	NTC			Thermistor	

Packaging instruction					
Standard packaging quantity (SPQ)	36	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 2 packages see vincotech.com website.

Package data
Package data for *flow* 2 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
V23990-P760-Ax -D8-14	26 Feb. 2018	R-Tau table corrected	10